



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = 25°C
20V	3.0Ω @ V _{GS} = 4.5V	240mA
	6.0Ω @ V _{GS} = 1.8V	170mA

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power management functions

Features and Benefits

- N-Channel MOSFET
- Low On-Resistance:
 - 3.0 Ω @ 4.5V
 - 4.0 Ω @ 2.5V
 - 6.0 Ω @ 1.8V
 - 10 Ω @ 1.5V
- Very Low Gate Threshold Voltage, 1.05V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package, 0.4mm Maximum Package Height
- ESD Protected Gate
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

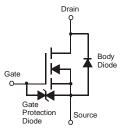
- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.001 grams (approximate)



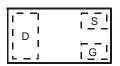




Bottom View



Equivalent Circuit



Top View

Ordering Information (Note 3)

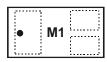
Part Number	Case	Packaging
DMN26D0UFB4-7	X2-DFN1006-3	3,000/Tape & Reel
DMN26D0UFB4-7B	X2-DFN1006-3	10,000/Tape & Reel

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

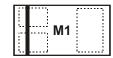
Marking Information

DMN26D0UFB4-7



Top View Dot Denotes Drain Side

DMN26D0UFB4-7B



Top View Bar Denotes Gate and Source Side

M1 = Product Type Marking Code



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
Drain Source Voltage	V _{DSS}	20	V		
Gate-Source Voltage	V _{GSS}	±10	V		
Continuous Drain Current (Note 4) V _{GS} = 4.5V	Steady State	$T_A = 25$ °C $T_A = 70$ °C	I _D	240 190	mA
Continuous Drain Current (Note 4) V _{GS} = 1.8V	I _D	180 140	mA		
Pulsed Drain Current - T _P = 10μs	I _{DM}	805	mA		

Thermal Characteristics @T_A = 25°C unless otherwise specified

Total Power Dissipation (Note 4) @T _A = 25°C	P _D	350	mW
Thermal Resistance, Junction to Ambient (Note 4)	$R_{ hetaJA}$	357	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

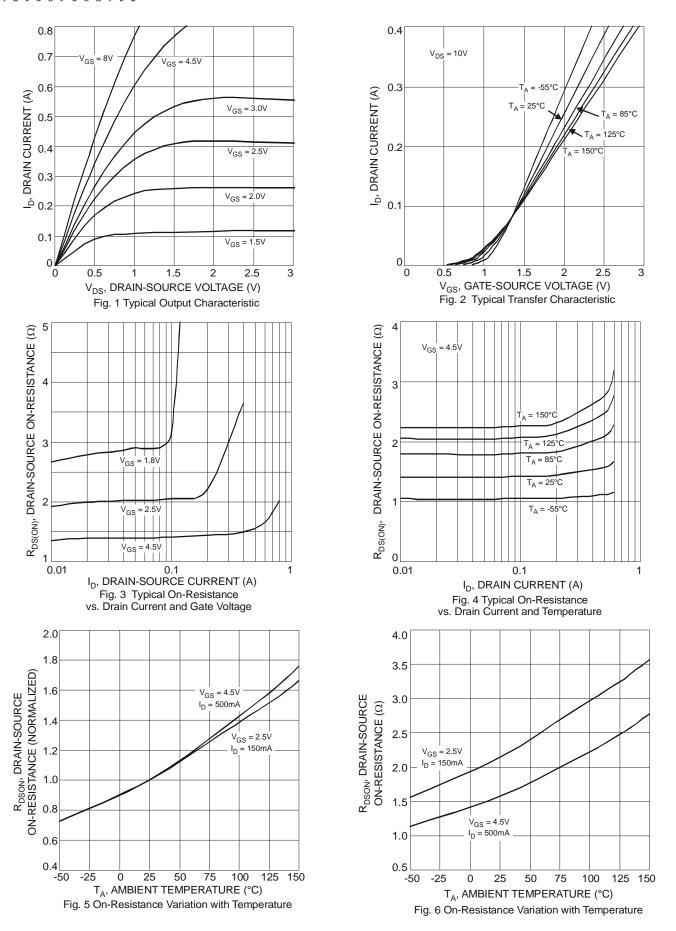
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 5)							
Drain-Source Breakdown Voltage	BV _{DSS}	20		_	V	$V_{GS} = 0V, I_D = 100 \mu A$	
Zero Gate Voltage Drain Current @ T _C = 25°C	I _{DSS}			500	nA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}	_	_	±1 ±100	μA nA	$V_{GS} = \pm 10V, V_{DS} = 0V$ $V_{GS} = \pm 5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 5)					I	00 - 7 50 -	
Gate Threshold Voltage	V _{GS(th)}	0.45		1.05	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R _{DS (ON)}		1.8 2.5 3.4 4.7	3.0 4.0 6.0 10.0	Ω	$V_{GS} = 4.5V, I_D = 100 \text{mA}$ $V_{GS} = 2.5V, I_D = 50 \text{mA}$ $V_{GS} = 1.8V, I_D = 20 \text{mA}$ $V_{GS} = 1.5V, I_D = 10 \text{mA}$	
Forward Transconductance	Y _{fs}	180	242	_	mS	$V_{DS} = 10V, I_{D} = 0.1A$	
Source-Drain Diode Forward Voltage	V _{SD}	0.5	_	1.4	V	V _{GS} = 0V, I _S = 115mA	
DYNAMIC CHARACTERISTICS							
Input Capacitance	Ciss		14.1	_	pF	151/1/ 01/	
Output Capacitance	Coss		2.9	_	pF	$V_{DS} = 15V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}		1.6	_	pF		
SWITCHING CHARACTERISTICS							
Turn-On Delay Time	t _{d(on)}	_	3.8	_			
Rise Time	t _r	_	7.9	_	ns	$V_{GS} = 4.5V, V_{DD} = 10V$	
Turn-Off Delay Time	t _{d(off)}	_	13.4	_	115	$I_D=200mA,\ R_G=2.0\Omega$	
Fall Time	t _f		15.2				

Notes:

- 4. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 5. Short duration pulse test used to minimize self-heating effect.







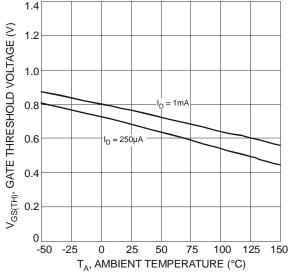
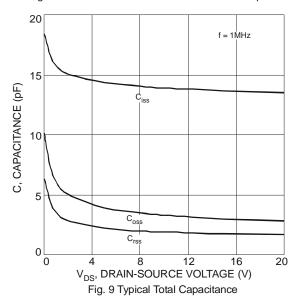
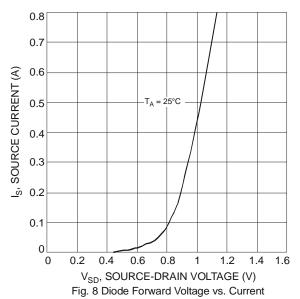


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





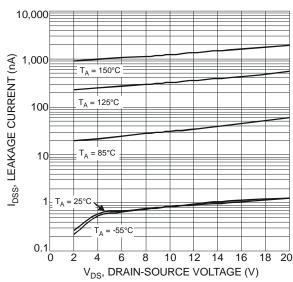


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

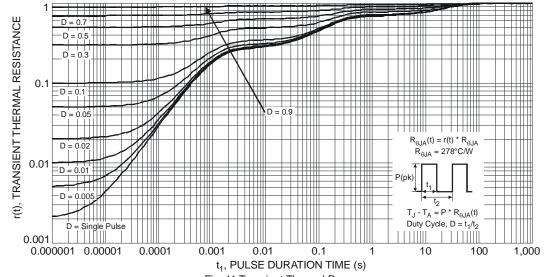
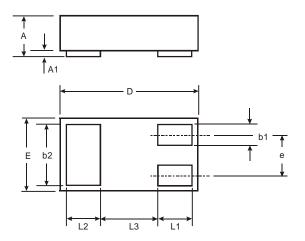


Fig. 11 Transient Thermal Response

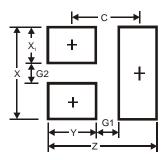


Package Outline Dimensions



	X2-DFN1006-3				
Dim	Min	Min Max			
Α		0.40			
A1	0	0.05	0.02		
b1	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.05	1.00		
Е	0.55	0.65	0.60		
е	_	_	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	_	_	0.40		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
Х	0.7
X1	0.25
Y	0.4
С	0.7



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